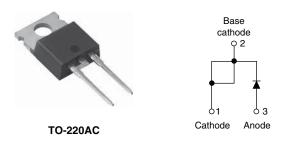
VS-8ETU04HN3

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Ultrafast Rectifier, 8 A FRED Pt[®]



PRODUCT SUMMARY									
Package	TO-220AC								
I _{F(AV)}	8 A								
V _R	400 V								
V _F at I _F	0.94 V								
t _{rr} typ.	See Recovery table								
T _J max.	175 °C								
Diode variation	Single die								

FEATURES

- Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- AEC-Q101 gualified, meets JESD 201, class 2 whisker test



• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

FRED Pt[®] series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance. ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		400	V						
Average rectified forward current	I _{F(AV)}	T _C = 155 °C	8							
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	100	А						
Repetitive peak forward current	I _{FRM}		16							
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	400	-	-					
Forward voltage	V _F	I _F = 8 A	-	1.19	1.3					
		I _F = 8 A, T _J = 150 °C	-	0.94	1.0					
Deverse leekege eurrent	I _R	V _R = V _R rated	-	0.2	10					
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	20	500	μA				
Junction capacitance	CT	V _R = 400 V	-	14	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

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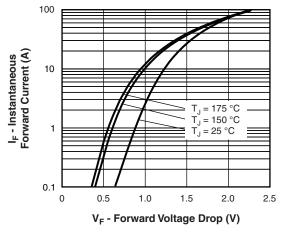


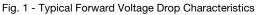
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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		I _F = 1.0 A, dI _F /dt =	50 A/µs, V _R = 30 V	-	35	60				
	t _{rr}	T _J = 25 °C		-	43	-	ns			
		T _J = 125 °C		-	67	-				
Dook rooovery ourrent	I _{RRM}	T _J = 25 °C	$I_F = 8 A$	-	2.8	-	٨			
Peak recovery current		IRRM	T _J = 125 °C	dl _F /dt = 200 A/µs V _R = 200 V	-	6.3	-	A		
Reverse recovery charge	0	T _J = 25 °C		-	60	-	nC			
	Q _{rr}	T _J = 125 °C		-	210	-	nc			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction to case	R _{thJC}		-	1.8	2					
Thermal resistance, junction to ambient	R _{thJA}	R _{thJA} Typical socket mount		-	50	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-					
M/aiabt			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC		8ETU04H						





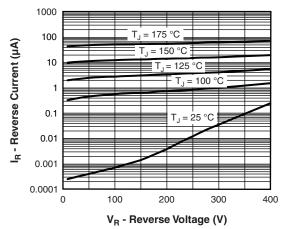


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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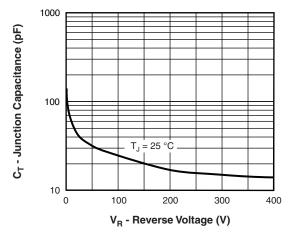


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

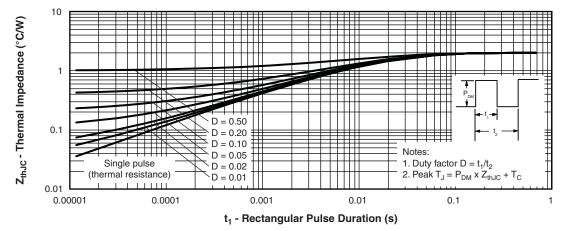
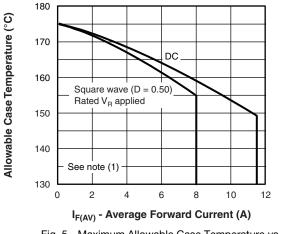
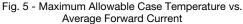


Fig. 4 - Maximum Thermal Impedance $\mathsf{Z}_{\mathsf{thJC}}$ Characteristics



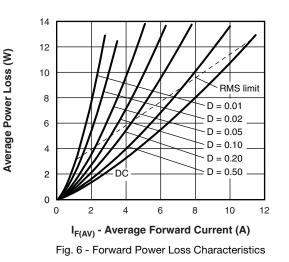
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Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$



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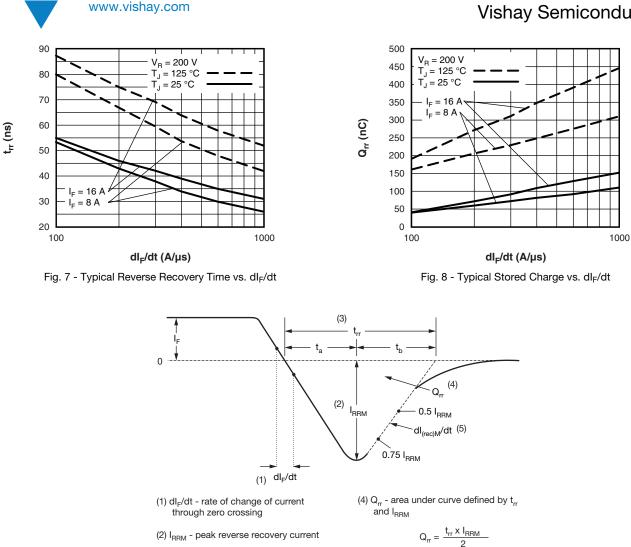
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(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

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(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	8	Е	т	U	04	н	N3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)
	<u> </u>	Visł	av Sen	niconduc	tors pro	oduct	0	\bigcirc
	2 -		•	ng (8 = 8	•			
	3 -		single c					
	4 -	Pac	kage:					
		T =	TO-220)				
	5 -	U =	ultrafas	t recove	ery			
	6 -	Volt	age rati	ng (04 =	= 400 V)			
	7 -	H =	AEC-Q	101 qua	lified			
	8 -	Env	ironmer	ntal digit	:			
		N3	= haloge	en-free,	RoHS-c	complia	nt, and t	otally le

ORDERING INFORMATION (Example)									
PREFERRED P/N	EFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIP								
VS-8ETU04HN3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95221							
Part marking information	www.vishay.com/doc?95068							
SPICE model	www.vishay.com/doc?95441							



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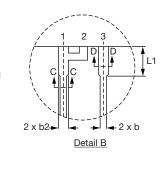
TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES		OTMEDEL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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